

1 Characteristics

Table 2. Absolute maximum ratings (limiting values; $T_j = 25\text{ °C}$, unless otherwise specified)

Symbol	Parameter			Value	Unit
$I_{T(RMS)}$	On-state rms current (full sine wave)		$T_c = 88\text{ °C}$	12	A
I_{TSM}	Non repetitive surge peak on-state current (full cycle, T_j initial = 25 °C)	$F = 50\text{ Hz}$	$t_p = 20\text{ ms}$	90	A
		$F = 60\text{ Hz}$	$t_p = 16.7\text{ ms}$	95	
I^2t	I^2t Value for fusing	$t_p = 10\text{ ms}$		54	A^2s
di/dt	Critical rate of rise of on-state current $I_G = 2 \times I_{GT}$ $t_r \leq 100\text{ ns}$	$F = 60\text{ Hz}$	$T_j = 125\text{ °C}$	50	$A/\mu s$
V_{DSM} , V_{RSM}	Non repetitive surge peak off-state voltage	$t_p = 10\text{ ms}$	$T_j = 25\text{ °C}$	V_{DRM} , V_{RRM} + 100	V
I_{GM}	Peak gate current	$t_p = 20\text{ }\mu s$	$T_j = 125\text{ °C}$	4	A
$P_{G(AV)}$	Average gate power dissipation		$T_j = 125\text{ °C}$	1	W
T_{stg}	Storage junction temperature range			- 40 to + 150	$^{\circ}C$
T_j	Operating junction temperature range			- 40 to + 125	$^{\circ}C$

Table 3. Electrical characteristics ($T_j = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)

Symbol	Test conditions	Quadrant		T12xxT				Unit
				T1210T	T1220T	T1225T	T1235T	
$I_{GT}^{(1)}$	$V_D = 12\text{ V}$ $R_L = 30\text{ }\Omega$	I - II - III	MAX.	10	20	25	35	mA
		IV				40		
V_{GT}	$V_D = V_{DRM}$, $R_L = 3.3\text{ k}\Omega$, $T_j = 25\text{ }^{\circ}\text{C}$	ALL	MAX.	1.3				V
V_{GD}	$V_D = V_{DRM}$, $R_L = 3.3\text{ k}\Omega$, $T_j = 125\text{ }^{\circ}\text{C}$	ALL	MIN.	0.2				V
$I_H^{(2)}$	$I_T = 500\text{ mA}$		MAX.	10	15	20	30	mA
I_L	$I_G = 1.2\text{ }I_{GT}$	I - III	MAX.	20	35	40	50	mA
		IV				40		
		II		30	40	60	80	
$dV/dt^{(2)}$	$V_D = 67\%\text{ }V_{DRM}$, gate open	$T_j = 125\text{ }^{\circ}\text{C}$	MIN.	100	1000	100	2000	V/ μs
		$T_j = 150\text{ }^{\circ}\text{C}^{(3)}$		50	500	50	1000	
$(dI/dt)_c^{(2)}$	$(dV/dt)_c = 0.1\text{ V}/\mu\text{s}$	$T_j = 125\text{ }^{\circ}\text{C}$	MIN.	7		7		A/ms
	$(dV/dt)_c = 10\text{ V}/\mu\text{s}$			3		3		
	Without snubber				6		12	
	$(dV/dt)_c = 0.1\text{ V}/\mu\text{s}$	$T_j = 150\text{ }^{\circ}\text{C}^{(3)}$		3		3		
	$(dV/dt)_c = 10\text{ V}/\mu\text{s}$			1		1		
	Without snubber				3		10	

1. Minimum I_{GT} is guaranteed at 5% of I_{GT} max.
2. For both polarities of A2 referenced to A1.
3. Derating information for excess temperature above T_j max.

Table 4. Static characteristics

Symbol	Test conditions			Value	Unit
V _T ⁽¹⁾	I _{TM} = 17 A, t _p = 380 μs	T _j = 25 °C	MAX.	1.55	V
V _{TO} ⁽¹⁾	Threshold voltage	T _j = 125 °C	MAX.	0.85	V
R _D ⁽¹⁾	Dynamic resistance	T _j = 125 °C	MAX.	35	mΩ
I _{DRM} I _{RRM}	V _{DRM} = V _{RRM}	T _j = 25 °C	MAX.	5	μA
		T _j = 125 °C		1	
	V _D = 0.9 x V _{DRM}	T _j = 150 °C ⁽²⁾	TYP.	1.9	mA

1. For both polarities of A2 referenced to A1.
2. Derating information for excess temperature above T_j max.

Table 5. Thermal resistance

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	Junction to case (AC)	2.6	$^{\circ}\text{C/W}$
$R_{th(j-a)}$	Junction to ambient (DC)	60	$^{\circ}\text{C/W}$

Figure 1. Maximum power dissipation versus rms on-state current (full cycle)

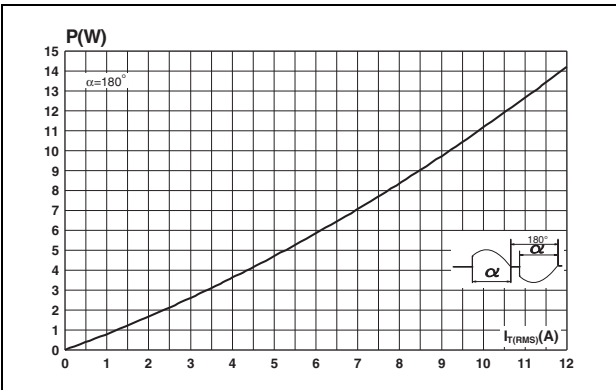


Figure 2. On-state rms current versus case temperature (full cycle)

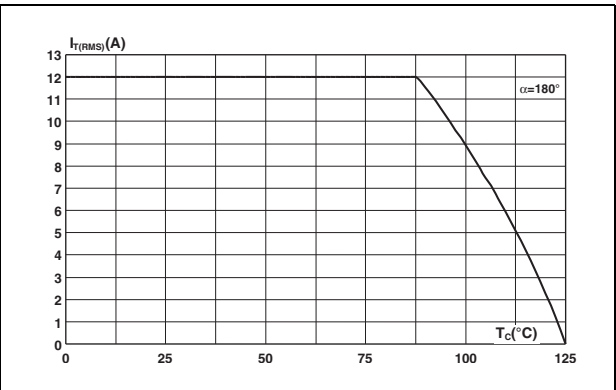


Figure 3. On-state rms current versus ambient temperature

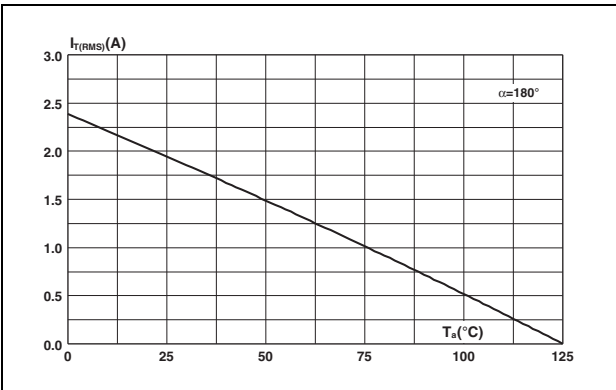


Figure 4. Relative variation of thermal impedance versus pulse duration

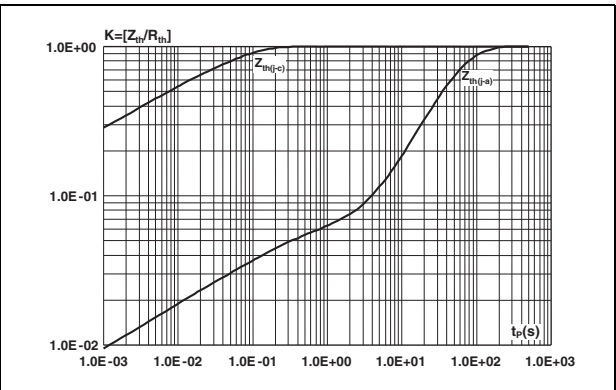


Figure 5. On state characteristics (maximum values)

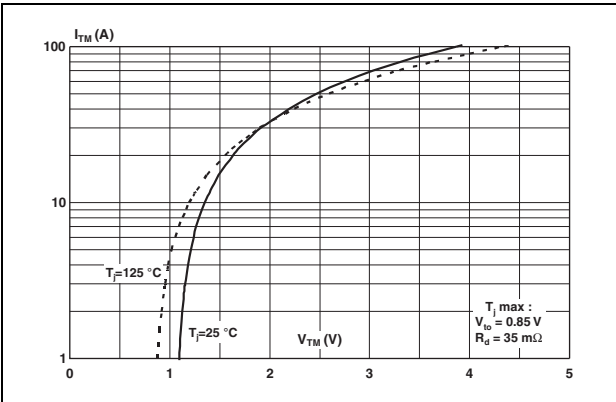


Figure 6. Surge peak on state current versus number of cycles

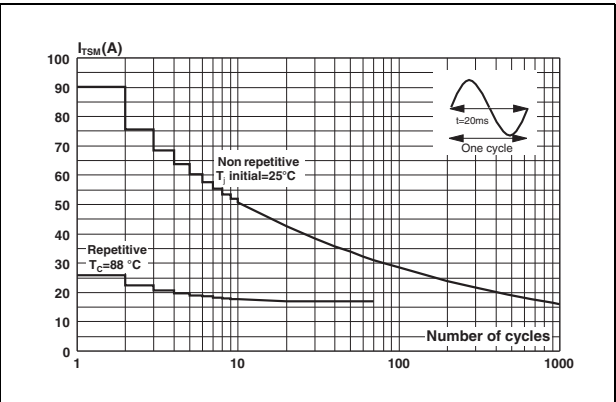


Figure 7. Non repetitive surge peak on state current for a sinusoidal

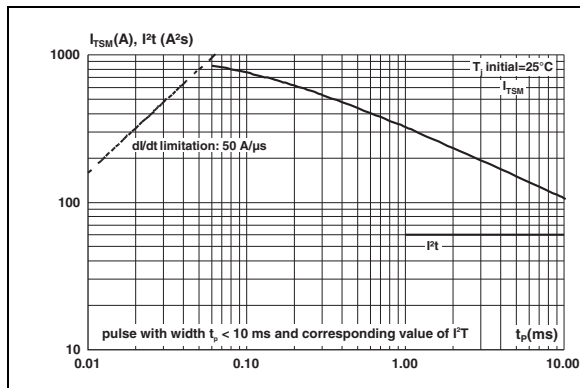


Figure 8. Relative variation of gate trigger current and gate trigger voltage versus junction temperature

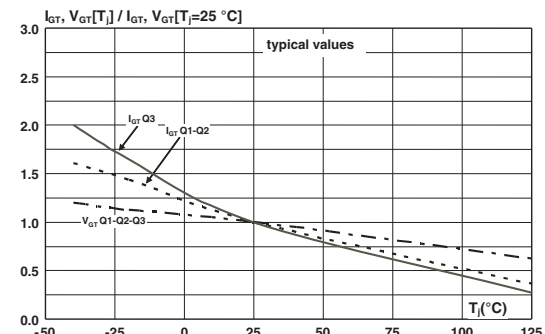


Figure 9. Relative variation of holding current and latching current versus junction temperature

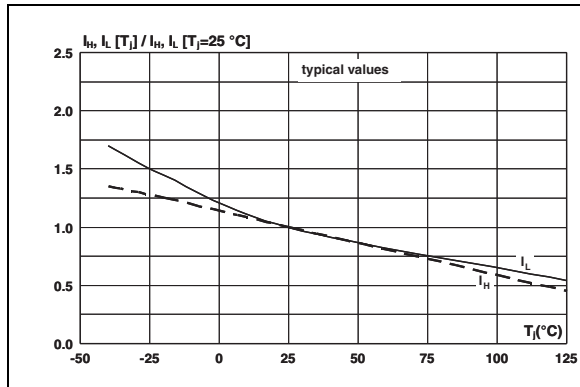


Figure 10. Relative variation of critical rate of decrease of main current versus (dV/dt)_c

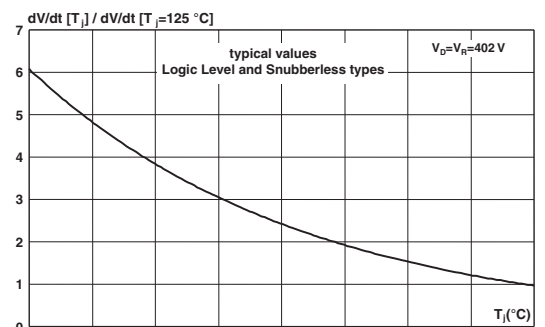


Figure 11. Relative variation of critical rate of decrease of main current versus junction temperature

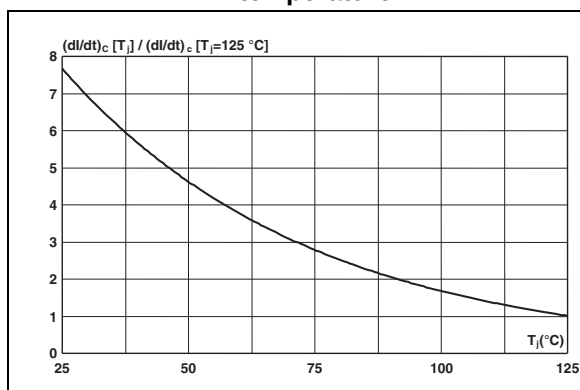
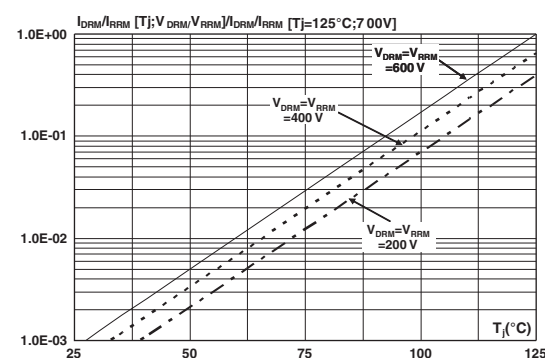


Figure 12. Leakage current versus junction temperature for different values of blocking voltage (typical values)



2 Package information

- Epoxy meets UL94, V0
- Lead-free packages

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

Table 6. TO-220AB insulated dimensions

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	15.20		15.90	0.598		0.625
a1		3.75			0.147	
a2	13.00		14.00	0.511		0.551
B	10.00		10.40	0.393		0.409
b1	0.61		0.88	0.024		0.034
b2	1.23		1.32	0.048		0.051
C	4.40		4.60	0.173		0.181
c1	0.49		0.70	0.019		0.027
c2	2.40		2.72	0.094		0.107
e	2.40		2.70	0.094		0.106
F	6.20		6.60	0.244		0.259
ØI	3.75		3.85	0.147		0.151
I4	15.80	16.40	16.80	0.622	0.646	0.661
L	2.65		2.95	0.104		0.116
I2	1.14		1.70	0.044		0.066
I3	1.14		1.70	0.044		0.066
M		2.60			0.102	

3 Ordering information

Figure 13. Ordering information scheme

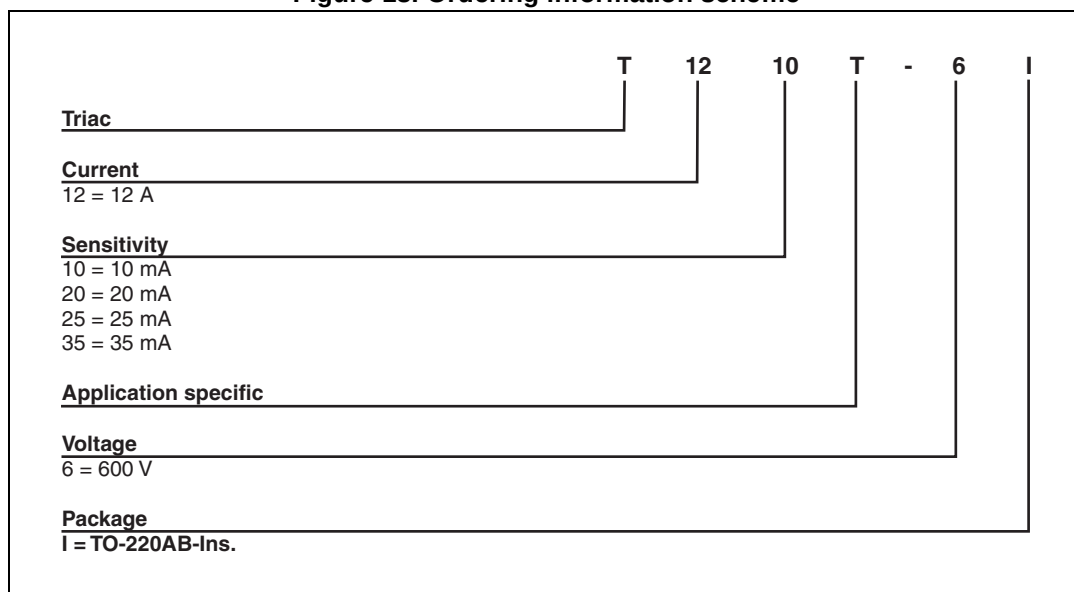


Table 7. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
T1210T-6I	T1210T-6I	TO-220AB-ins.	2.3 g	50	Tube
T1220T-6I	T1220T-6I				
T1225T-6I	T1225T-6I				
T1235T-6I	T1235T-6I				

4 Revision history

Table 8. Document revision history

Date	Revision	Changes
03-Dec-2009	1	Initial release.
18-Jan-2010	2	Updated pag.1.
16-Sep-2013	3	Updated: Features . Replaced order codes with part numbers in Table 1 .

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